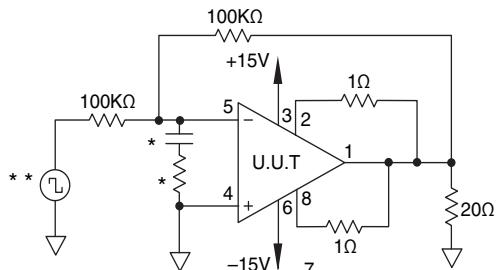**TABLE 4 GROUP A INSPECTION**

PA51M/883

HTTP://WWW.APEXMICROTECH.COM   (800) 546-APEX   (800) 546-2739

SG	PARAMETER	SYMBOL	TEMP.	POWER	TEST CONDITIONS	MIN	MAX	UNITS
1	Quiescent current	I_Q	25°C	±34V	$V_{IN} = 0$, $A_V = 100$, $R_{CL} = .1\Omega$		10	mA
1	Input offset voltage	V_{OS}	25°C	±34V	$V_{IN} = 0$, $A_V = 100$		±10	mV
1	Input offset voltage	V_{OS}	25°C	±10V	$V_{IN} = 0$, $A_V = 100$		±16	mV
1	Input offset voltage	V_{OS}	25°C	±40V	$V_{IN} = 0$, $A_V = 100$		±11.2	mV
1	Input bias current, +IN	$+I_B$	25°C	±34V	$V_{IN} = 0$		±40	nA
1	Input bias current, – IN	$-I_B$	25°C	±34V	$V_{IN} = 0$		±40	nA
1	Input offset current	I_{OS}	25°C	±34V	$V_{IN} = 0$		±10	nA
3	Quiescent current	I_Q	−55°C	±34V	$V_{IN} = 0$, $A_V = 100$, $R_{CL} = .1\Omega$		10	mA
3	Input offset voltage	V_{OS}	−55°C	±34V	$V_{IN} = 0$, $A_V = 100$		±15.2	mV
3	Input offset voltage	V_{OS}	−55°C	±10V	$V_{IN} = 0$, $A_V = 100$		±21.2	mV
3	Input offset voltage	V_{OS}	−55°C	±40V	$V_{IN} = 0$, $A_V = 100$		±16.4	mV
3	Input bias current, +IN	$+I_B$	−55°C	±34V	$V_{IN} = 0$		±72	nA
3	Input bias current, –IN	$-I_B$	−55°C	±34V	$V_{IN} = 0$		±72	nA
3	Input offset current	I_{OS}	−55°C	±34V	$V_{IN} = 0$		±26	nA
2	Quiescent current	I_Q	125°C	±34V	$V_{IN} = 0$, $A_V = 100$, $R_{CL} = .1\Omega$		13	mA
2	Input offset voltage	V_{OS}	125°C	±34V	$V_{IN} = 0$, $A_V = 100$		±16.5	mV
2	Input offset voltage	V_{OS}	125°C	±10V	$V_{IN} = 0$, $A_V = 100$		±22.5	mV
2	Input offset voltage	V_{OS}	125°C	±40V	$V_{IN} = 0$, $A_V = 100$		±17.7	mV
2	Input bias current, +IN	$+I_B$	125°C	±34V	$V_{IN} = 0$		±80	nA
2	Input bias current, –IN	$-I_B$	125°C	±34V	$V_{IN} = 0$		±80	nA
2	Input offset current	I_{OS}	125°C	±34V	$V_{IN} = 0$		±30	nA
4	Output voltage, I_O =10A	V_O	25°C	±18V	$R_L = 1\Omega$	10		V
4	Output voltage, I_O = 68mA	V_O	25°C	±40V	$R_L = 500\Omega$	34		V
4	Output voltage, I_O = 4A	V_O	25°C	±30V	$R_L = 6\Omega$	24		V
4	Current limits	I_{CL}	25°C	±16V	$R_L = 1\Omega$, $R_{CL} = .1\Omega$	5	7.9	A
4	Stability/noise	E_N	25°C	±34V	$R_L = 500\Omega$, $A_V = +1$, $C_L = 1.5nF$		1	mV
4	Slew rate	SR	25°C	±34V	$R_L = 500\Omega$	1.0	10	V/μs
4	Open loop gain	A_{OL}	25°C	±34V	$R_L = 500\Omega$, F = 10Hz	94		dB
4	Common-mode rejection	CMR	25°C	±15V	$R_L = 500\Omega$, F = DC, $V_{CM} = ±9V$	70		dB
6	Output voltage, I_O =10A	V_O	−55°C	±18V	$R_L = 1\Omega$	10		V
6	Output voltage, I_O = 68mA	V_O	−55°C	±40V	$R_L = 500\Omega$	34		V
6	Output voltage, I_O = 4A	V_O	−55°C	±30V	$R_L = 6\Omega$	24		V
6	Stability/noise	E_N	−55°C	±34V	$R_L = 500\Omega$, $A_V = +1$, $C_L = 1.5nF$		1	mV
6	Slew rate	SR	−55°C	±34V	$R_L = 500\Omega$	1.0	10	V/μs
6	Open loop gain	A_{OL}	−55°C	±34V	$R_L = 500\Omega$, F = 10Hz	94		dB
6	Common-mode rejection	CMR	−55°C	±15V	$R_L = 500\Omega$, F = DC, $V_{CM} = ±9V$	70		dB
5	Output voltage, I_O = 8A	V_O	125°C	±16V	$R_L = 1\Omega$	8		V
5	Output voltage, I_O = 68mA	V_O	125°C	±40V	$R_L = 500\Omega$	34		V
5	Output voltage, I_O = 4A	V_O	125°C	±30V	$R_L = 6\Omega$	24		V
5	Stability/noise	E_N	125°C	±34V	$R_L = 500\Omega$, $A_V = +1$, $C_L = 1.5nF$		1	mV
5	Slew rate	SR	125°C	±34V	$R_L = 500\Omega$	1.0	10	V/μs
5	Open loop gain	A_{OL}	125°C	±34V	$R_L = 500\Omega$, F = 10Hz	94		dB
5	Common-mode rejection	CMR	125°C	±15V	$R_L = 500\Omega$, F = DC, $V_{CM} = ±9V$	70		dB

BURN IN CIRCUIT

*   These components are used to stabilize device due to poor high frequency characteristics of burn in board.

**   Input signals are calculated to result in internal power dissipation of approximately 2.1W at case temperature = 125°C.